

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_H	$I_T=500mA$		MAX.	40	mA
dV/dt	$V_D=670V$ Gate Open $T_j=25$		MIN.	800	V/s
$(dI/dt)_c$	$T_j=125$		MIN.	10	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	7	s
t_{off}				50	

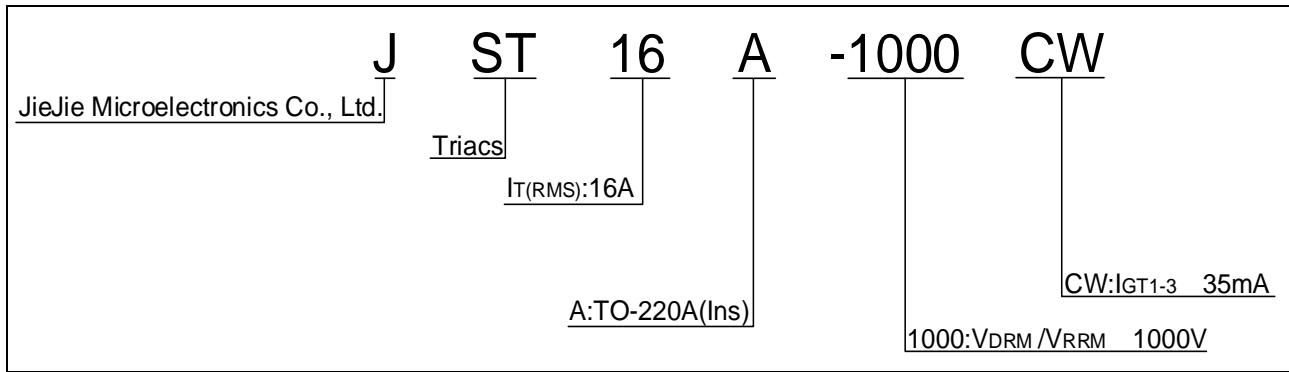
STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit	
V_{TM}	$I_{TM}=22.5A t_p=380 s$ $T_j=25$	1.5	V	
V_{TO}	Threshold voltage $T_j=125$	0.77	V	
R_D	Dynamic resistance $T_j=125$	32		
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	A
I_{RRM}		$T_j=125$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

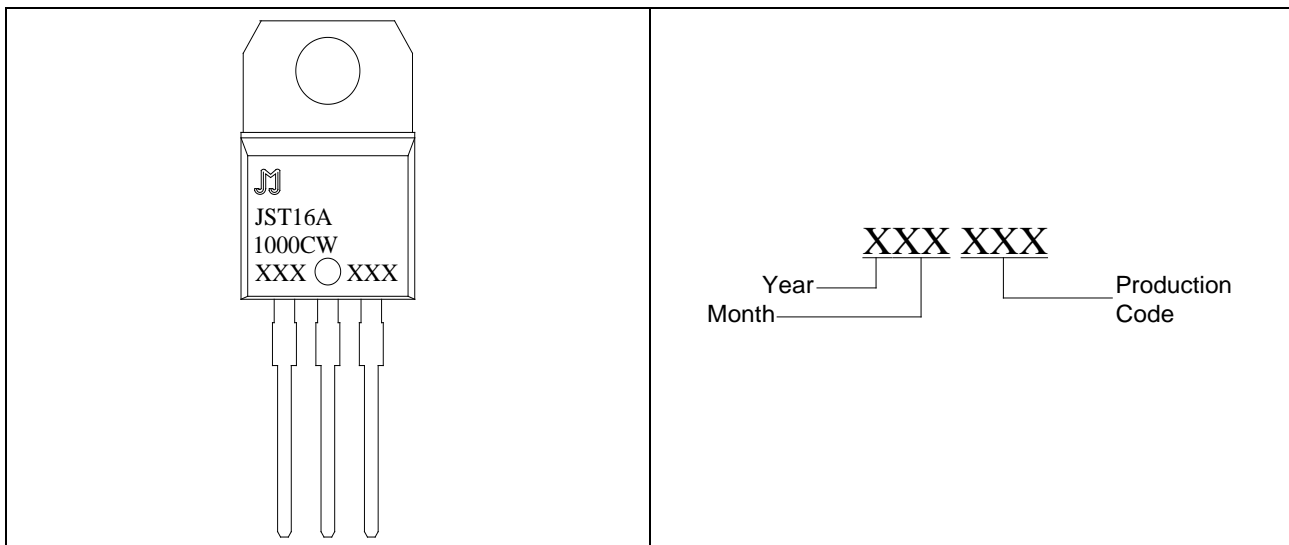


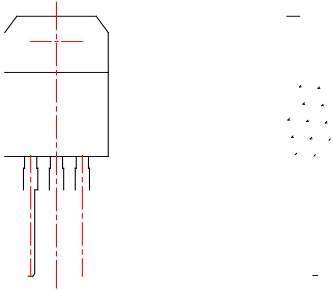
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA



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